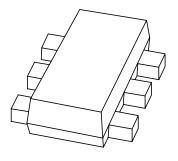
DISCRETE SEMICONDUCTORS

DATA SHEET



PEMZ7 NPN/PNP general purpose transistors

Product data sheet Supersedes data of 2001 Sep 25 2001 Nov 07



NPN/PNP general purpose transistors

PEMZ7

FEATURES

- 300 mW total power dissipation
- Very small 1.6 × 1.2 mm ultra thin package
- Self alignment during soldering due to straight leads
- Low collector capacitance
- Low V_{CEsat}
- · High current capabilities
- Improved thermal behaviour due to flat leads
- · Reduced required PCB area
- Reduced pick and place costs.

APPLICATIONS

- Heavy duty battery powered equipment (automotive, telecom and audio-video) such as motor and lamp drivers
- V_{CEsat} critical applications such as latest low supply voltage IC applications
- All battery driven equipment, to save battery power.

DESCRIPTION

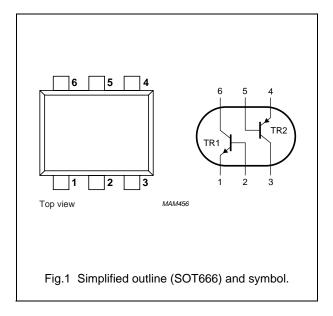
NPN/PNP low V_{CEsat} transistor pair in a SOT666 plastic package.

MARKING

TYPE NUMBER	MARKING CODE		
PEMZ7	Z7		

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transis	Per transistor; for the PNP transistor with negative polarity					
V _{CBO}	collector-base voltage	open emitter	-	15	V	
V_{CEO}	collector-emitter voltage	open base	_	12	٧	
V _{EBO}	emitter-base voltage	open collector	_	6	٧	
I _C	collector current (DC)		_	500	mA	
I _{CM}	peak collector current		-	1	А	
I _{BM}	peak base current		_	100	mA	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		_	150	°C	
T _{amb}	operating ambient temperature		-65	+150	°C	
Per device	•					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	300	mW	

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	DL PARAMETER CONDITIONS		VALUE	UNIT	
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W	

Notes

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering method is reflow soldering.

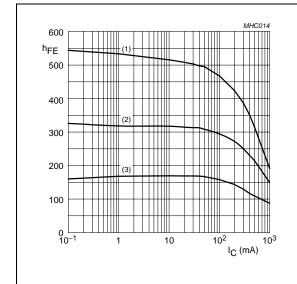
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CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor; for the PNP transistor with negative polarity					
I _{CBO}	collector-base cut-off current	V _{CB} = 15 V; I _E = 0	_	_	100	nA
		V _{CB} = 15 V; I _E = 0; T _j = 150 °C	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0$	_	_	100	nA
h _{FE}	DC current gain	$V_{CE} = 2 \text{ V}; I_{C} = 10 \text{ mA}$	200	-	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 200 \text{ mA}; I_B = 10 \text{ mA}$	_	_	220	mV
f _T	transition frequency	$I_C = 100 \text{ mA}; V_{CE} = 5 \text{ V};$				
	TR1 (NPN)	f = 100 MHz	250	420	_	MHz
	TR2 (PNP)		100	280	_	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$				
	TR1 (NPN)		_	4.4	6	pF
	TR2 (PNP)		_	_	10	pF



TR1 (NPN); $V_{CE} = 2 V$.

- (1) T_{amb} = 150 °C.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.2 DC current gain as a function of collector current; typical values.

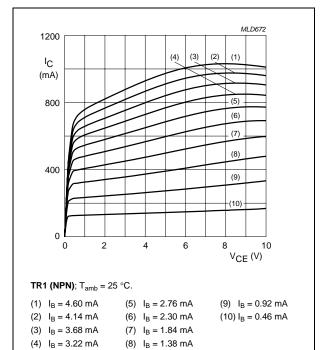
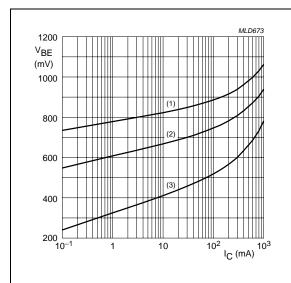


Fig.3 Collector current as a function of collector-emitter voltage; typical values.

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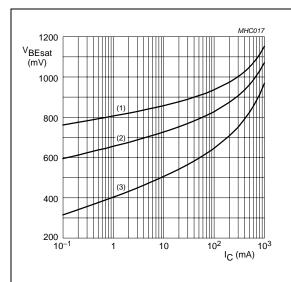
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TR1 (NPN); $V_{CE} = 2 V$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

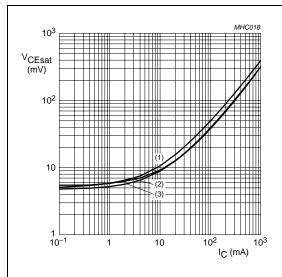
Fig.4 Base-emitter voltage as a function of collector current; typical values.



TR1 (NPN); $I_C/I_B = 20$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

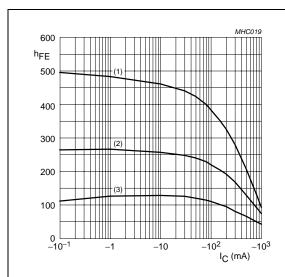
Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.



TR1 (NPN); $I_C/I_B = 20$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.6 Collector-emitter saturation voltage as a function of collector current; typical values.



TR2 (PNP); $V_{CE} = -2 \text{ V}.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \,^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.7 DC current gain as a function of collector current; typical values.

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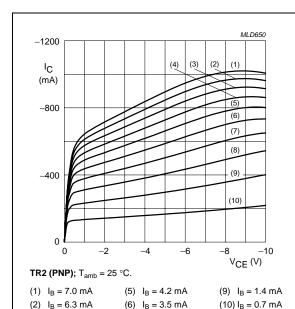


Fig.8 Collector current as a function of collector-emitter voltage; typical values.

(7) $I_B = 2.8 \text{ mA}$

(8) $I_B = 2.1 \text{ mA}$

(3) $I_B = 5.6 \text{ mA}$

(4) $I_B = 4.9 \text{ mA}$

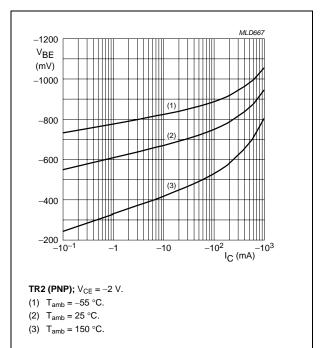


Fig.9 Base-emitter voltage as a function of collector current; typical values.

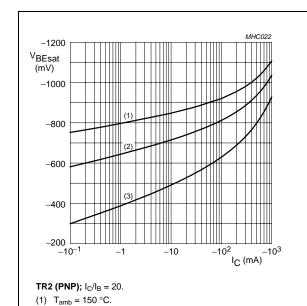
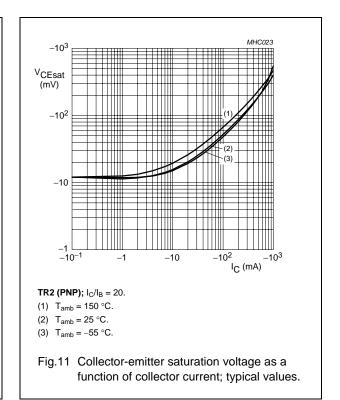


Fig.10 Base-emitter saturation voltage as a function of collector current; typical values.



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(2) $T_{amb} = 25 \, ^{\circ}C$. (3) $T_{amb} = -55 \, ^{\circ}C$.

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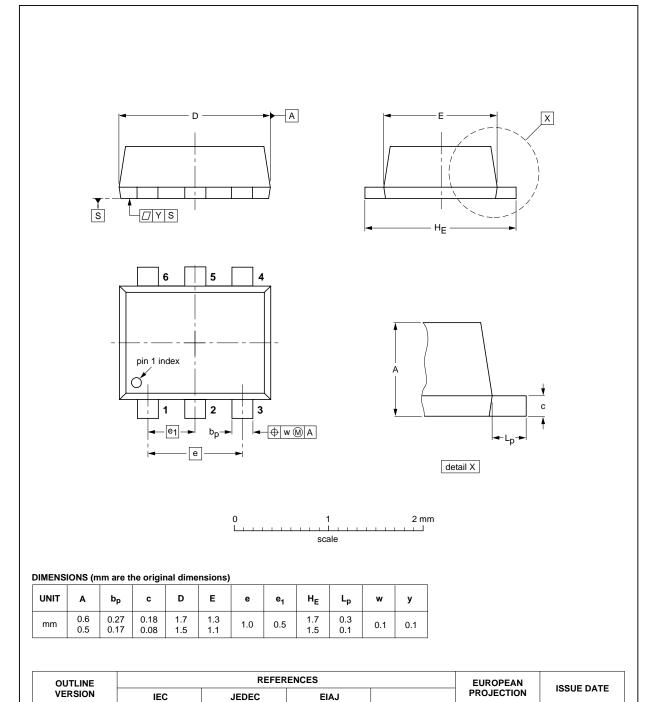
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



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SOT666

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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